503734051 03/11/2016 PATENT ASSIGNMENT COVER SHEET

Electronic Version v1.1 Stylesheet Version v1.2 EPAS ID: PAT3780693

SUBMISSION TYPE:		NEW ASSIGNMENT		
NATURE OF CONVEYANCE:		RELEASE OF SECURITY INTEREST		
CONVEYING PARTY D	АТА			
		Name	Execution Date	
FIDUS MEZZANINE CA	PITAL II, L.F).	03/11/2016	
RECEIVING PARTY DA	ТА			
Name:	CTG ADV	CTG ADVANCED MATERIALS, LLC		
Street Address:	479 QUAD	RANGLE DRIVE SUITE-E		
City:	BOLINGB	ROOK		
State/Country:	ILLINOIS			
Postal Code:	60440			
	ł			
PROPERTY NUMBERS	Total: 10			
Property Type		Number		
Patent Number:	694	42730		
Patent Number:	Patent Number: 7908			
Patent Number: 8535		35442		
Patent Number: 8559		59273		
Application Number: 1302		025751		
Application Number:				
Application Number:	139	957074		
		019750		
Application Number:	618	303025		
Application Number:	618	349058		
CORRESPONDENCE D	ΑΤΑ			
Fax Number:	•	7)573-5850		
			is unsuccessful, it will be sent	
Phone:	umber, if provided; if that is unsuccessful, it will be sent via US Mail. 6175735850			
Email:	elizabeth.burkhard@hklaw.com			
Correspondent Name:				
Address Line 1:				
Address Line 4: BOSTON, MASSACHUSETTS 02116			116	

SIGNATURE:	/Elizabeth Burkhard/	
DATE SIGNED:	03/11/2016	
Total Attachments: 6		
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RELEASE OF GRANT OF SECURITY INTEREST IN PATENTS

WHEREAS, CTG ADVANCED MATERIALS, LLC, a Delaware limited liability company (the "<u>Pledgor</u>"), is the owner of the patents and patent applications listed on <u>Schedule A</u> attached hereto, (all such patents, registrations and applications, collectively, the "<u>Patents</u>"); and

WHEREAS, in order to secure certain indebtedness, the Pledgor entered into a Pledge and Security Agreement (as amended, modified, restated or supplemented from time to time, the "Security Agreement") dated as of October 11, 2013, in favor of Fidus Mezzanine Capital II, L.P., as Collateral Agent (the "Collateral Agent"), and pursuant thereto executed and delivered a Grant of Security Interest in the Patents ("Grant") as recorded on October 11, 2013 with the United States Patent and Trademark Office on Reel 031395 at Frame 0906 pursuant to which the Pledgor granted to the Collateral Agent, according to the terms of the Security Agreement, a security interest in all of its right, title and interest in and to the Patents;

NOW, THEREFORE, for good and valuable consideration, the receipt and sufficiency of which are hereby acknowledged, the Collateral Agent does hereby release and relinquish, and, to the extent that Collateral Agent has acquired any right, title or interest in or to any of the Patents, does hereby reassign to the Pledgor, without representation or warranty, all of the Collateral Agent's right, title and interest in and to the Patents listed on the attached <u>Schedule A</u>, together with all proceeds and products thereof, and does hereby agree that the filing of the Grant in the United States Patent and Trademark Office as aforesaid may be removed of record.

FIDUS MEZZANINE CAPITAL II, L.P., as Collateral Agent

By: Fidus Investment GP, LLC, its General Partner

By: Fidus Investment Advisors, LLC, its Manager

By: 2. Carlo 2. A. Name: 10. Andrew Warth Title: Marager

Signature Page to Release of Security Interest in Patents - CTG

> PATENT REEL: 037960 FRAME: 0570

Schedule A

PATENT AND PATENT APPLICATIONS

Registered Patents:

Ожвег	Patent Number	Patent
CTG Advanced Materiais, LLC	6,942,730	HYBRID STOCKBARGER ZONE-
		LEVELING MELTING METHOD
		FOR DIRECTED
		CRYSTALLIZATION AND
		GROWTH OF SINGLE
		CRYSTALS OF LEAD
		MAGNESIUM NIOBATE-LEAD
		TITANATE (PMN-PT) SOLID
		SOLUTIONS AND RELATED
		PIEZOCRYSTALS
CTG Advanced Materials, LLC	7,908,722	A PROCESS FOR THE
		PREPARATION OF
		PIEZOELECTRIC CRYSTAL
		ELEMENTS
CTG Advanced Materials, LLC	8,535,442	CRYSTAL GROWTH SYSTEM
		AND METHOD FOR LEAD-
		CONTAINED COMPOSITIONS
		USING BATCH AUTO-FEEDING
CTG Advanced Materials, LLC	8,559,273	HIGH FREQUENCY
		PIEZOELECTRIC CRYSTAL
		COMPOSITES, DEVICES, AND
		METHOD FOR
		MANUFACTURING THE SAME

Applications:

Owner	Application Number	Description
CTG Advanced Materials, LLC	13/025,751	PROCESS FOR THE
		PREPARATION OF
		PIEZOELECTRIC CRYSTAL
		ELEMENTS AND A PRODUCT
		THEREOF
CTG Advanced Materials, LLC	13/821,400	HIGH FREQUENCY
		PIEZOELECTRIC CRYSTAL
		COMPOSITES, DEVICES, AND
		METHODS FOR
		MANUFACTURING THE SAME
CTG Advanced Materials, LLC	13/957,074	CRYSTAL GROWTH SYSTEM
		AND METHOD FOR LEAD-
		CONTAINED COMPOSITIONS
		USING BATCH AUTO-FEEDING
CTG Advanced Materials, LLC	14/019,750	HIGH FREQUENCY
		PIEZOELECTRIC CRYSTAL
	······	COMPOSITES, DEVICES AND

Owner	Application Number	Description
		METHODS FOR
		MANUFACTURING THE SAME
CTG Advanced Materials, LLC	61/803,025	APPARATUS AND PROCESS
		FOR THE PREPARATION OF
		PIEZOELECTRIC CRYSTAL
		ELEMENTS AND SYSTEMS
		THEREOF
CTG Advanced Materials, LLC	61/849.058	TITLE ON COVER SHEET FOR
		PROVISIONAL APPLICATION
		(PTO/SB/16):
		NEW TYPE ELECTRO-OPTICAL
		SINGLE CRYSTAL ELEMENTS,
		ITS' APPLICATIONS AND THE
		PREPARATION PROCESSES
		THEREOF
		TITLE ON ASSIGNMENT AND
		ON APPLICATION AS FILED:
		PIEZOELECTRIC CRYSTAL
	×.	ELEMENTS OF D24 SHEAR
		MODE, APPLICATIONS AND
		PROCESSES FOR THE
		PREPARATION THEREOF
		TITLE ON NOTICE OF
		RECORDATION:
		TYPE ELECTRO-OPTICAL
		SINGLE CRYSTAL ELEMENTS,
		ITS' APPLICATIONS AND THE
		PREPARATION PROCESSES
		THEREOF
CTG Advanced Materials, LLC	60/330,915 (Expired)	HYBRID STOCKBARGER ZONE-
		LEVELING MELTING METHOD
		FOR DIRECT
1		CRYSTALLIZATION AND
		GROWTH OF
CTG Advanced Materials, LLC	60/598,885 (Expired)	PIEZOELECTRIC CRYSTAL
		ELEMENTS OF SHEAR MODE
		AND PROCESS FOR THE
	+ 1 () AM (10) + 2 + 1 + 1 + 1	PREPARATION THEREOF
CTG Advanced Materials, LLC	11/182,704 (Abandoned)	PIEZOELECTRIC CRYSTAL
		ELEMENTS OF SHEAR MODE
		AND PROCESS FOR THE PREDADATION THEREOF
CTC Advanced & Samuelake TX C	11/205 875 / 4 band and	PREPARATION THEREOF HYBRID STOCKBARGER ZONE-
CTG Advanced Materials, LLC	11/205,875 (Abandoned)	LEVELING MELTING METHOD
1		FOR DIRECT
		CRYSTALLIZATION AND
		GROWTH OF
OTO A transit Material XI C	LAN220 120 / Frankrich	CRYSTAL GROWTH METHOD
CTG Advanced Materials, LLC	60/830,139 (Expired)	
L		FOR LEAD-CONTAINING

Owner	Application Nomber	Description
		COMPOSITIONS USING BATCH
		AUTO-FEEDING
CTG Advanced Materials, LLC	PCT/US2007/073412 (Expired)	CRYSTAL GROWTH METHOD
		FOR LEAD-CONTAINING
		COMPOSITIONS USING BATCH
		AUTO-FEEDING
CTG Advanced Materials, LLC	11/818,735 (Abandoned)	PIEZOELECTRIC CRYSTAL
		ELEMENTS OF SHEAR MODE
		AND PROCESS FOR THE
		PREPARATION THEREOF
CTG Advanced Materials, LLC	12/212,445 (Abandoned)	HYBRID STOCKBARGER ZONE-
		LEVELING MELTING METHOD
		FOR DIRECT
		CRYSTALLIZATION AND
		GROWTH OF
CTG Advanced Materials, LLC	PCT/US2011/56230 (Expired)	HIGH FREQUENCY
		PIEZOELECTRIC CRYSTAL
		COMPOSITES, DEVICES, AND
		METHOD FOR
		MANUFACTURING THE SAME
CTG Advanced Materials, LLC	PCT/US2011/56231 (Expired)	HIGH FREQUENCY
		PIEZOELECTRIC CRYSTAL
		COMPOSITES, DEVICES, AND
	i · · ·	METHOD FOR
CORP. 4 X	<u> </u>	MANUFACTURING THE SAME
CTG Advanced Materials, LLC	61/344,801 (Expired)	HIGH FREQUENCY (20-100MHZ) PMN-PT-BASED
		PEZOELECTRIC CRYSTAL
		COMPOSITES COMPOSITE-
		CRYSTAL-ELEMENT, AND THE
		PREPARATION PROCESSES
		THEREOF
		I FRANKLAP

OTHER PATENTS:

Applications:

Owner	Country	Application Number	Description
CTG Advanced Materials,	China	CN201180047348	HIGH FREQUENCY
LLC			PIEZOELECTRIC
			CRYSTAL
			COMPOSITES,
			DEVICES, AND
			METHODS FOR
			MANUFACTURING THE
			SAME
CTG Advanced Materials,	Japan	JP2013-534959	HIGH FREQUENCY

Owner	Country	Application Number	Description
LLC			PIEZOELECTRIC
			CRYSTAL
			COMPOSITES,
			DEVICES, AND
			METHODS FOR
			MANUFACTURING THE
			SAME
CTG Advanced Materials,	South Korea	KR10-2013-7007909	HIGH FREQUENCY
LLC			PIEZOELECTRIC
			CRYSTAL
-			COMPOSITES,
			DEVICES, AND
			METHODS FOR
			MANUFACTURING THE
			SAME
CTG Advanced Materials,	China	CN201180047368.8	HIGH FREQUENCY
uc			PIEZOELECTRIC
			CRYSTAL
			COMPOSITES.
			DEVICES, AND
			METHOD FOR
			MANUFACTURING THE
1		ł	SAME
CTG Advanced Materials,	Japan	JP2013-534960	HIGH FREQUENCY
LLC			PIEZOELECTRIC
			CRYSTAL
			COMPOSITES,
			DEVICES, AND
			METHOD FOR
			MANUFACTURING THE
			SAME
CTG Advanced Materials,	South Korea	KR20-2013-7007910	HIGH FREQUENCY
LLC	1		PIEZOELECTRIC
			CRYSTAL
			COMPOSITES,
			DEVICES, AND
			METHOD FOR
			MANUFACTURING THE
			SAME